

1. Scope :

This specification applies to NIP silicon photodiode chips,
Device No. PD-2062

2. Structure :

- 2-1. Planar type : NIP diode.
- 2-2. Electrodes :
Top side(Cathode & Anode): Aluminum alloy.
Back side (Anode) : Gold alloy.

3. Size :

- 3-1. Chip size : 63 mils × 63 mils (1.6 mm × 1.6 mm).
- 3-2. Chip thickness : 12 ± 1.5mils (0.305 ± 0.038 mm).
- 3-3. Active area : 53 mils × 53 mils (1.346 mm × 1.346 mm).
- 3-4. Bonding pad (Cathode) : 6 mils × 6 mils (0.153 mm × 0.153 mm)
- 3-5. Pattern drawing : Refer to the attaché

4. Electro-optical characteristics (Ta = 25 °C)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Reverse dark current	I_D	$V_R=10V$ $E_e=0mW/cm^2$			10	nA
Reverse breakdown voltage	$V_{(BR)R}$	$I_R=100\mu A$ $E_e=0mW/cm^2$	60			V
Open circuit voltage	V_{oc}	$T=2856K$ $E_e=5mW/cm^2$		410		mV
Short circuit Current	I_{sc}	$T=2856K$ $E_e=5mW/cm^2$		17		μA
Reverse light current	I_L	$V_R =5V$ $T=2856K$ $E_e=5mW/cm^2$		17		μA
Total Capacitance	C_t	$V_R =5V$ $E_e=0mW/cm^2$ $f=1MHz$		5		pF
Turn-on/ Turn-off Time	T_{on}/t_{off}	$\lambda =905nm$ $V_R=10V$ $R_L=1000\Omega$		200/200		ns

*Based on 100% probing

